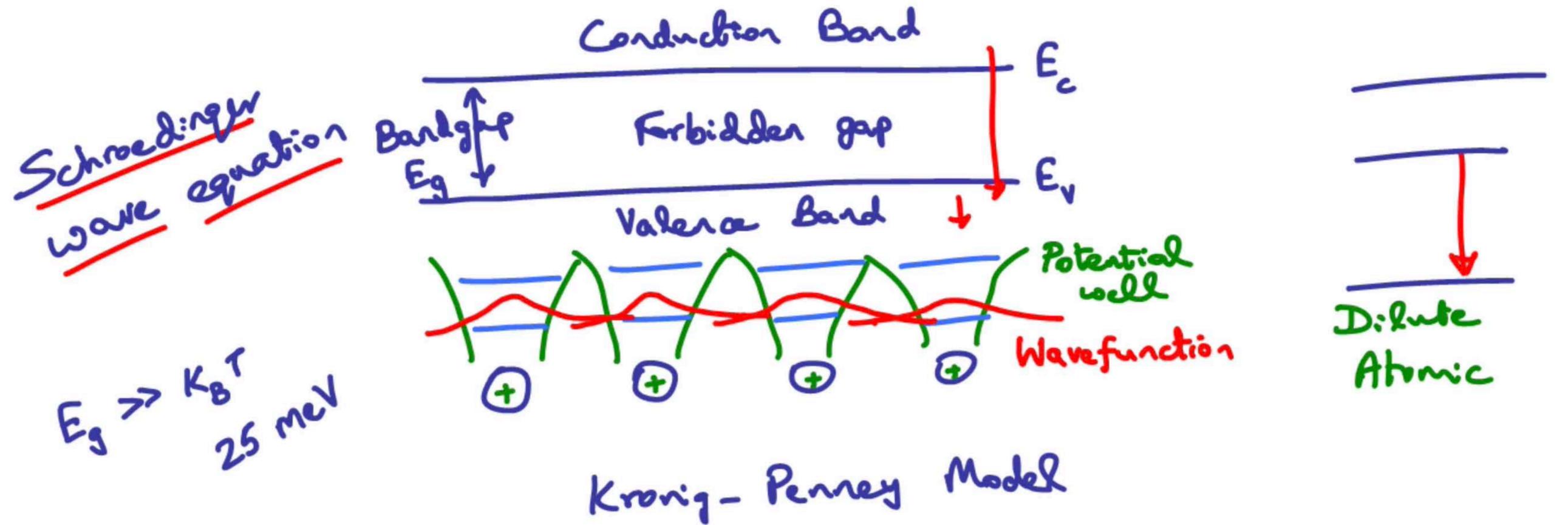
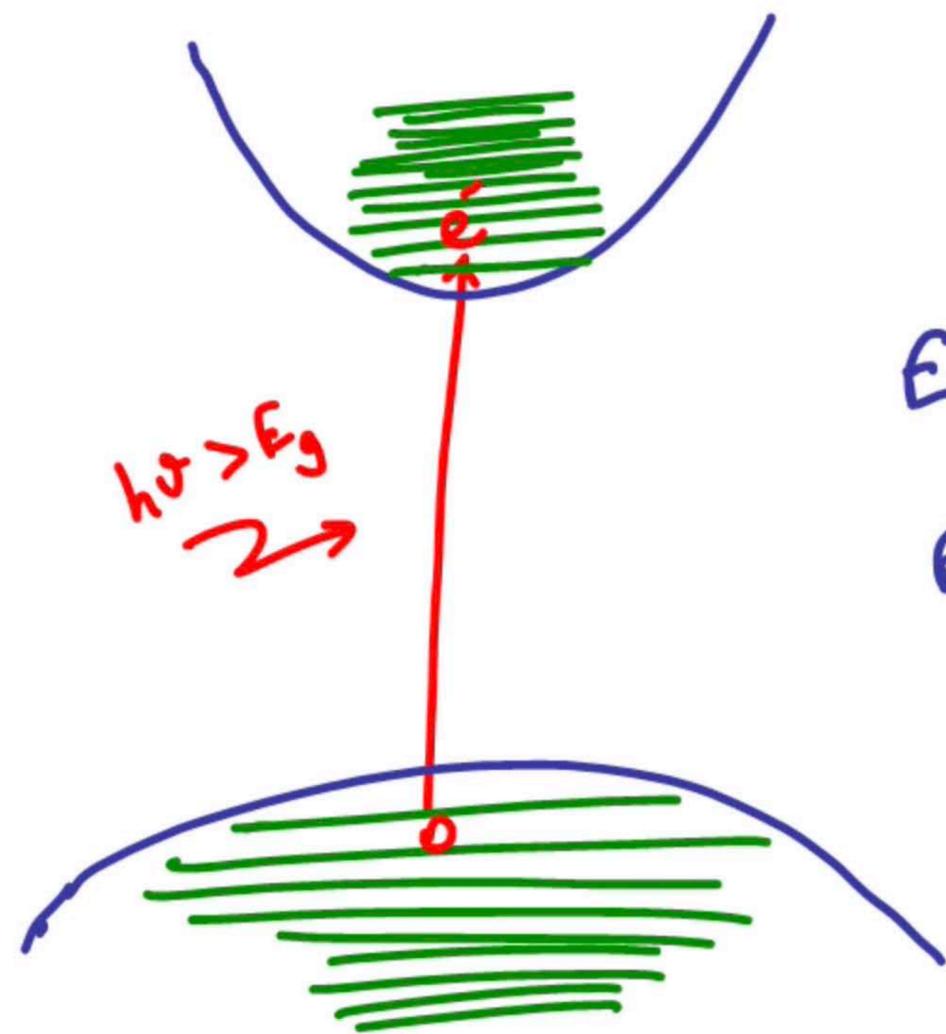


# Learning Objective: Identify fundamental principles of semiconductor light sources & detectors



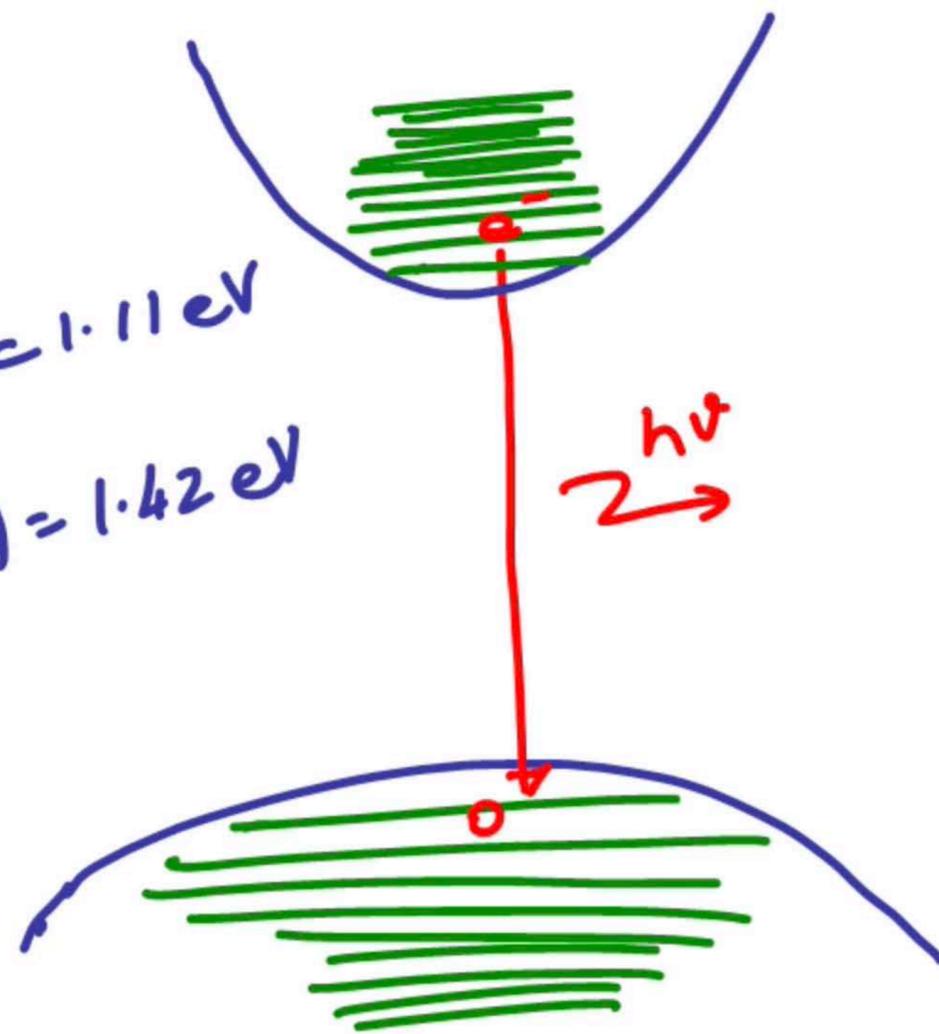
Schrodinger  
wave equation

$E_g \gg k_B T$   
25 meV

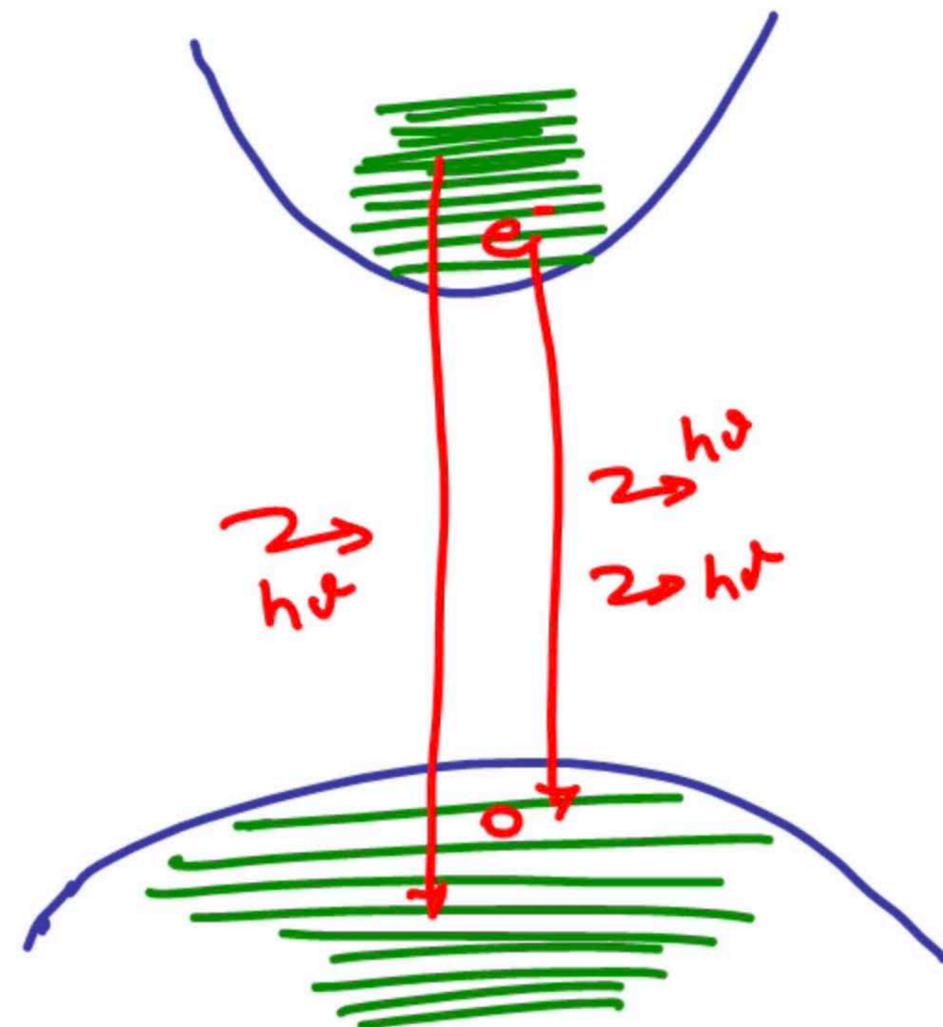


Absorption

$$E_g(\text{Si}) = 1.11 \text{ eV}$$
$$E_g(\text{GaAs}) = 1.42 \text{ eV}$$

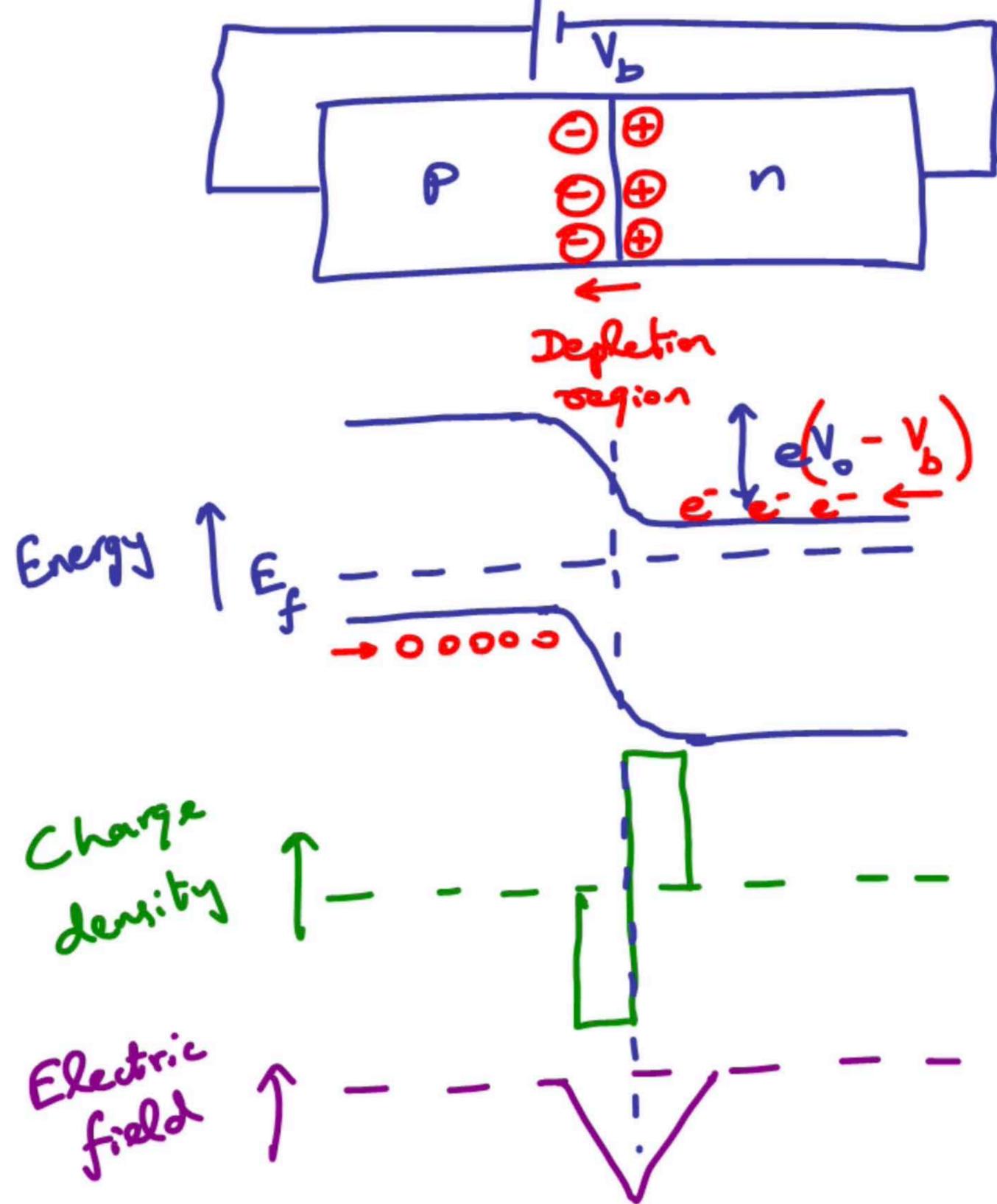
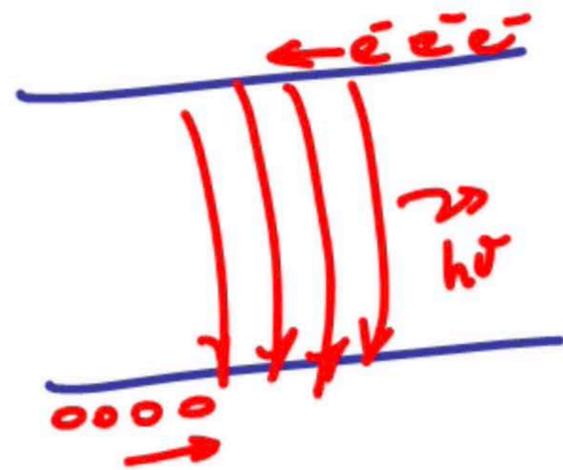


Spontaneous emission

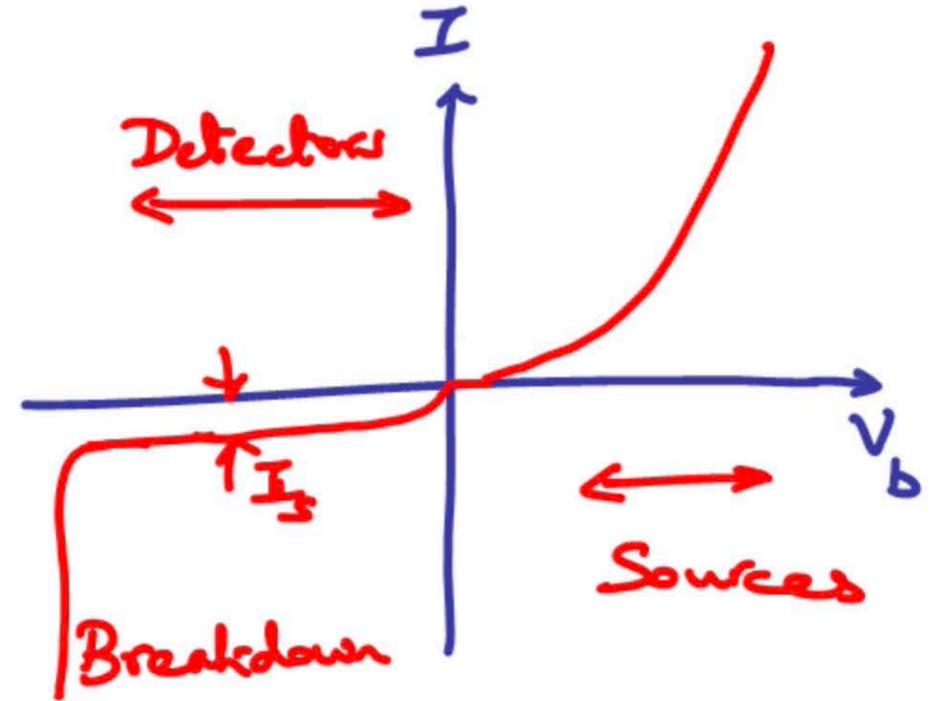


Stimulated emission

# PN Junctions



$$I = I_s \exp\left(\frac{eV_b}{k_B T}\right) - I_s$$

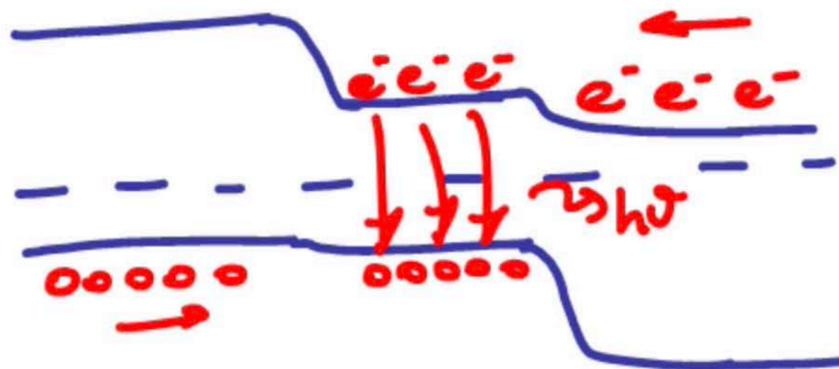
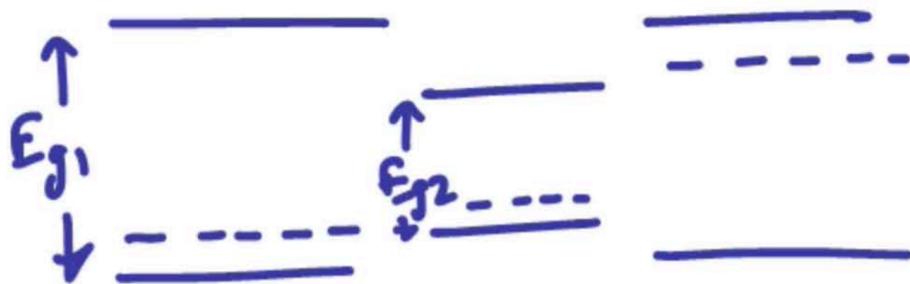
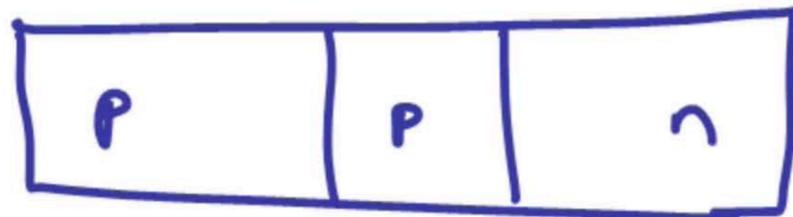


Gauss Law

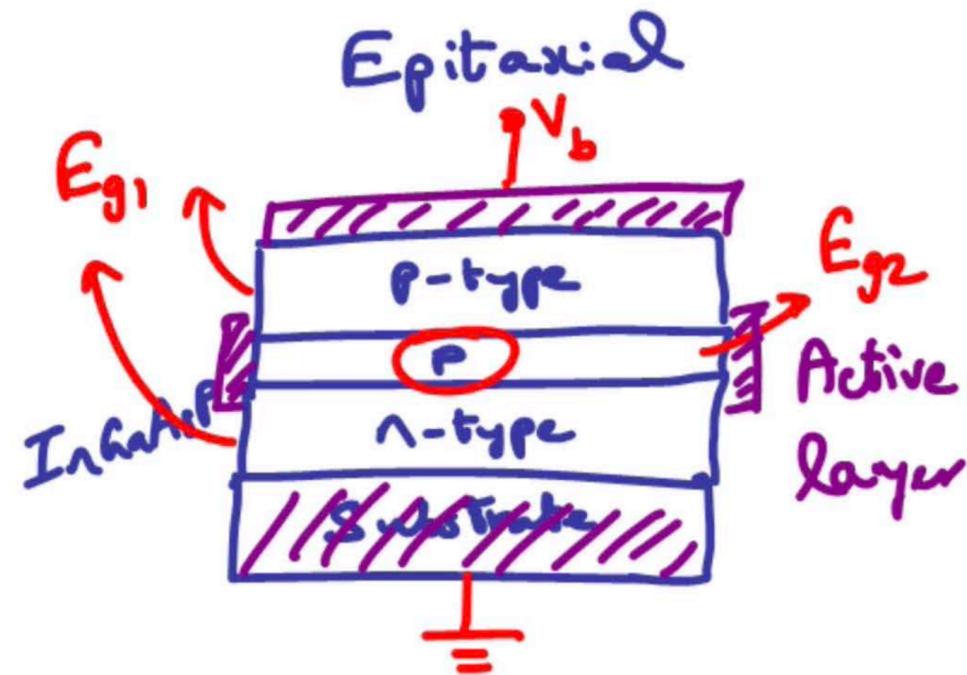
$$\nabla \cdot \vec{D} = \rho_v$$

# Heterostructure

Carrier &  
Light  
Confinement



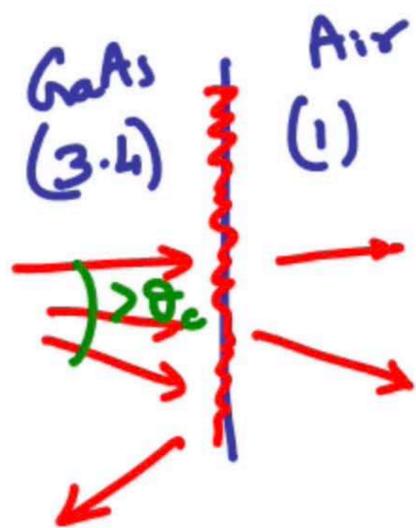
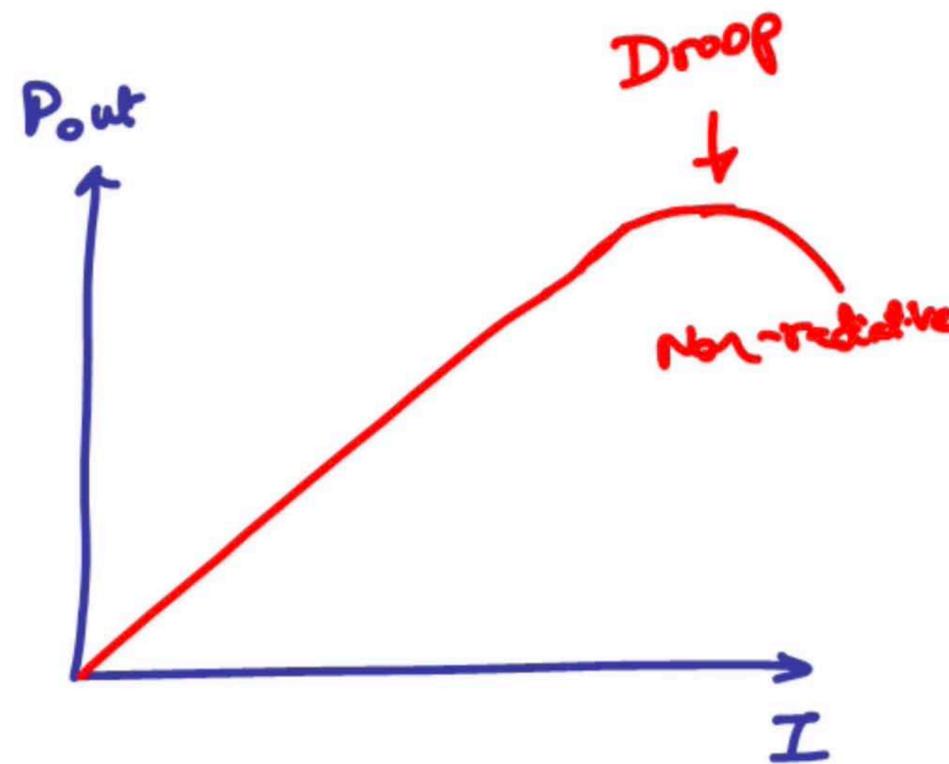
Refractive index  $\uparrow$



# Light Emitting Diodes

Output Power.  $P_{out} = \frac{I}{e} h\nu \eta_{int} \eta_{out}$

$$\frac{R_{rad}}{R_{rad} + R_{non-rad}} = \frac{\tau_{nr}}{\tau_r + \tau_{nr}} \sim 80-90\%$$



$$R = \left(\frac{n-1}{n+1}\right)^2 \Rightarrow T = 1 - \left(\frac{n-1}{n+1}\right)^2 = \frac{4n}{(n+1)^2}$$

Fraction of light escaping  $\left. \vphantom{\frac{4n}{(n+1)^2}} \right\} = 1 - \cos \theta_c = 1 - \sqrt{1 - \left(\frac{1}{n}\right)^2} \approx \frac{1}{2n^2}$

$$\eta_{out} = \frac{4n}{(n+1)^2} \cdot \frac{1}{2n^2} = \frac{2}{n(n+1)^2}$$